

ABSTRACT

The present invention relates to a SiC material and a method for manufacturing same and, more particularly, to a SiC material and a method for manufacturing same, wherein the SiC material includes a SiC layer having a low thermal conductivity region formed in at least
5 a portion thereof, wherein the low thermal conductivity region has an average crystal grain size of 3.5 μm or less and (111) plane preferential growth according to X-ray diffraction analysis.